V_{DSS}	20 V
I_D	7 A
$R_{DS(ON)}$	12mΩ

ANVV

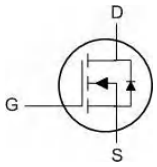
Description

The SI2312A is the hihgcell densit tryenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The SI2312A meet the RoHS and Green Product requirement with full function reliability approved.

Features

Green Device Available
Super Low Gate Charge
Excellent Cdv/dt effect decline
Advanced high cell density Trench technology



Schematic Diagram



SOT-23-3L top view

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 4.5V[1]	7.0	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 4.5V[1]	5.0	A
I_{DM}	Pulsed Drain Current[2]	32	A
P_D@T_A=25℃	Total Power Dissipation[3]	2	W
P_D@T_A=70℃	Total Power Dissipation[3]	0.66	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	120	℃/W

Electrical Characteristics (T_J=25℃unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS} =±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.5	0.75	1.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}=4.5V, I_D=6A	-	12	15	mΩ
		V_{GS}=2.5V, I_D=5A	-	16	22.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f=1.0MHz	-	700	-	pF
C_{oss}	Output Capacitance		-	132	-	pF
C_{rss}	Reverse Transfer Capacitance		-	114	-	pF
Q_g	Total Gate Charge	V_{DS}=10V, I_D=4A, V_{GS}=4.5V	-	15	-	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	5.2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V, I_D=4A, R_{GEN}=3Ω, V_{GS}=4.5V	-	9	-	ns
t_r	Turn-on Rise Time		-	25	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	37	-	ns
t_f	Turn-off Fall Time		-	14	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

RATING AND CHARACTERISTIC CURVES

Figure1: Output Characteristics

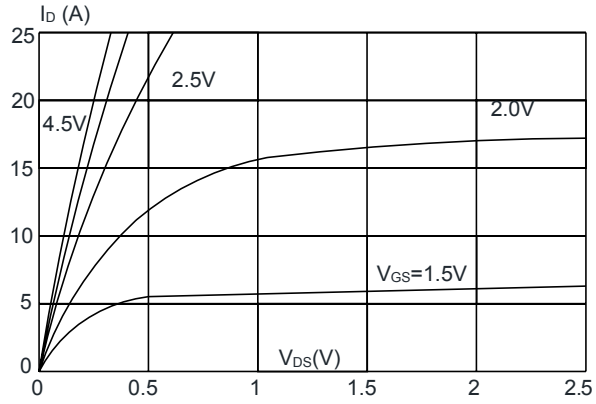


Figure 2: Typical Transfer Characteristics

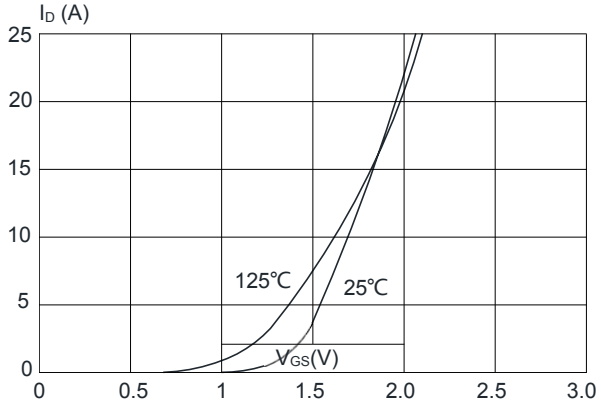


Figure 3: On-resistance vs. Drain Current

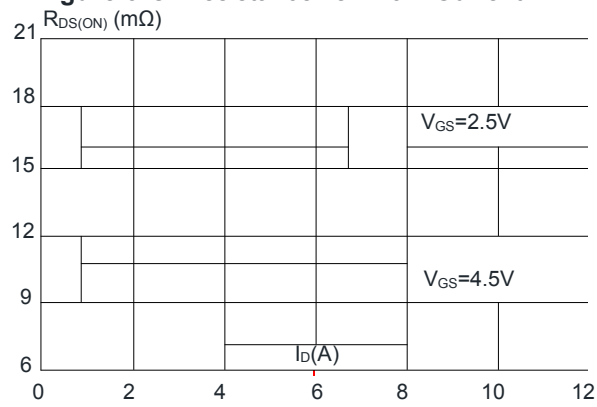


Figure 4: Body Diode Characteristics

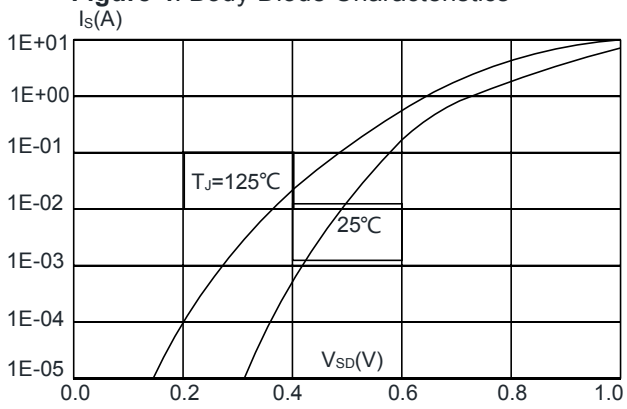


Figure 5: Gate Charge Characteristics

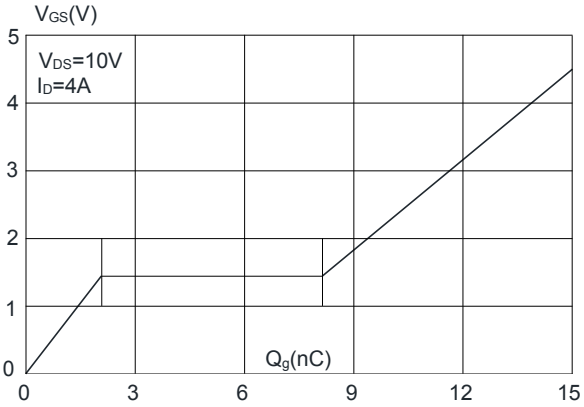
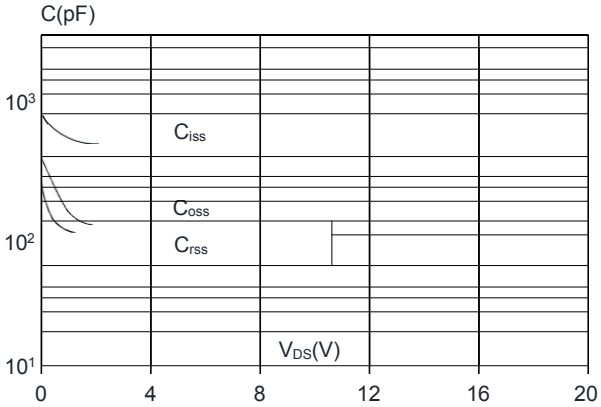


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

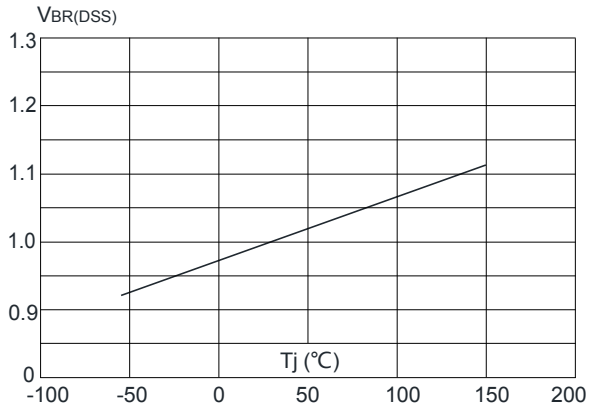


Figure 8: Normalized on Resistance vs. Junction Temperature

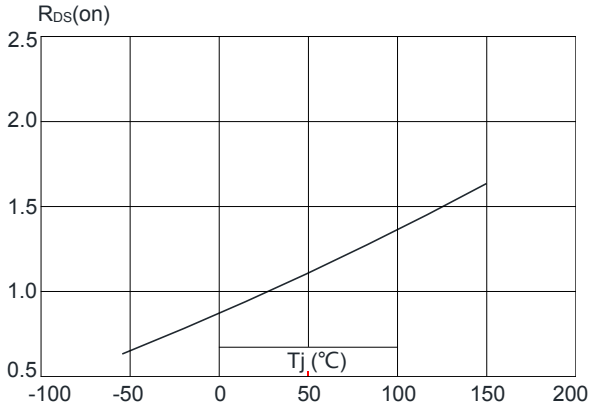


Figure 9: Maximum Safe Operating Area

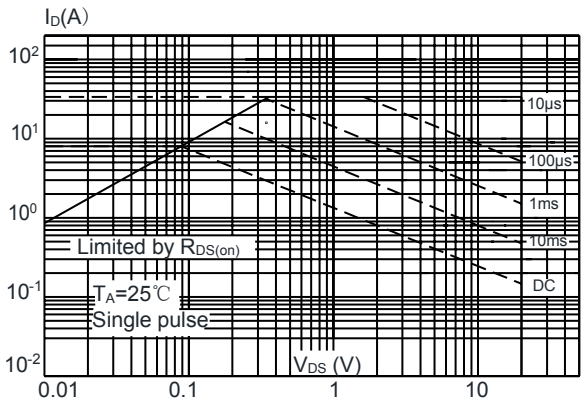


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

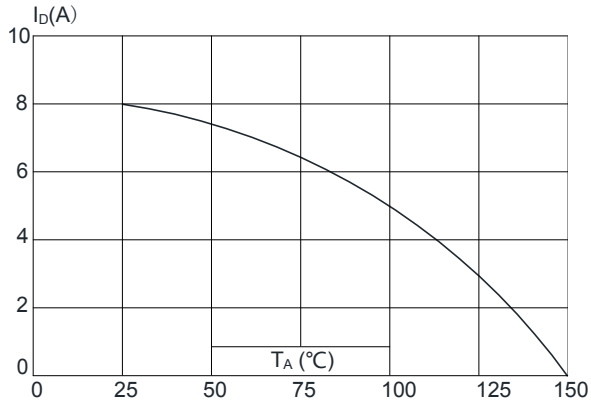
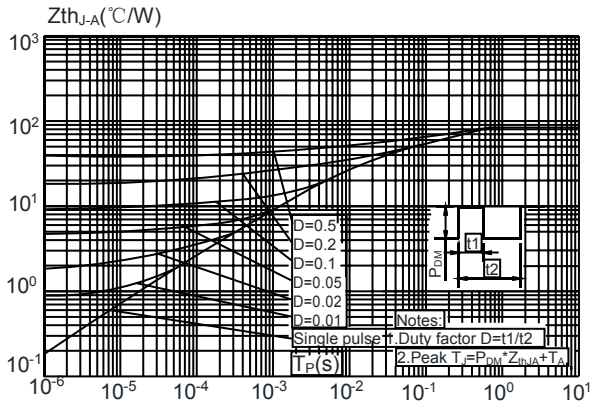


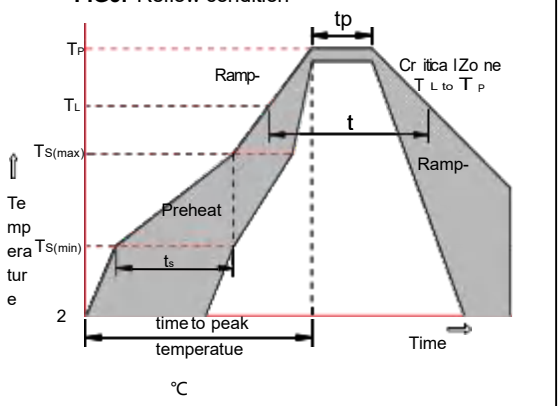
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Soldering parameters

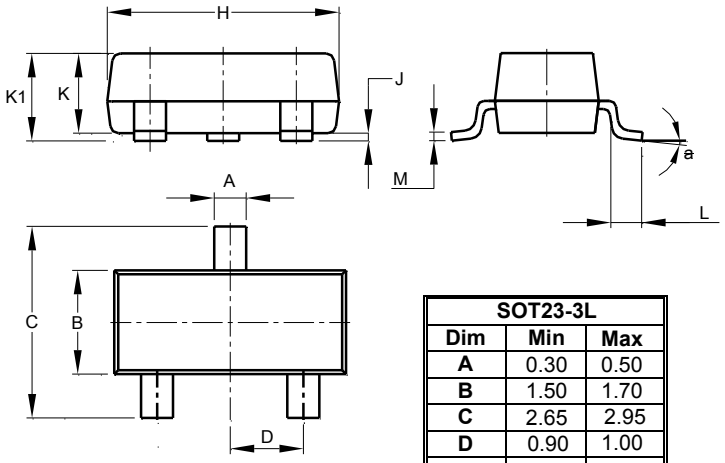
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition

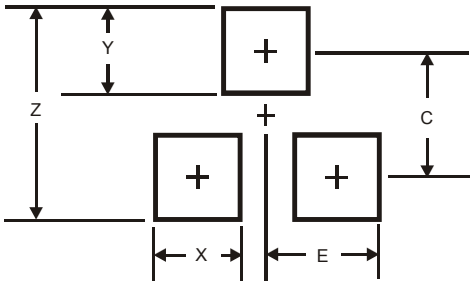


Package Dimensions & Suggested Pad Layout

SOT23-3L



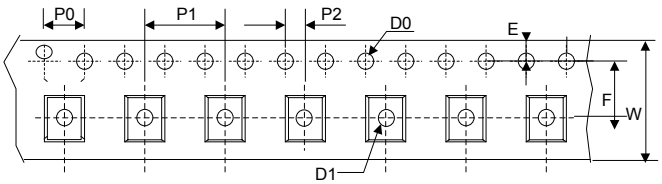
SOT23-3L		
Dim	**Min**	**Max**
A	0.30	0.50
B	1.50	1.70
C	2.65	2.95
D	0.90	1.00
H	2.82	3.02
J		0.10
K	1.05	1.15
K1	1.05	1.25
L	0.30	0.60
M	0.10	0.20
a	0°	8°
All Dimensions in mm		

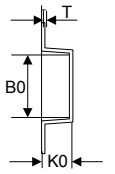


Dimensions	SOT23-3L
Z	3.3
X	0.9
Y	1.0
C	2.3
E	1.40

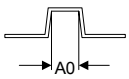
Tape & rell specification

Tape





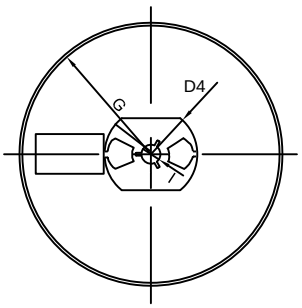
SECTION : B-B

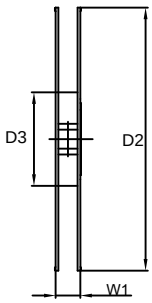


SECTION : A-A

Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.05±0.20
E	1.55±0.20
F	3.60±0.20
W	8.00±0.20
A0	3.80±0.20
B0	3.50±0.20
K0	1.55±0.20
T	0.25±0.15

7” Reel





D2	178.0±5.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0

Quantity: 3000PCS

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